Kenji Iso

List of Publications by Citations

28 papers	585 citations	12 h-index	24 g-index
29 ext. papers	630 ext. citations	2.1 avg, IF	3.02 L-index

#	Paper	IF	Citations
28	High Brightness Blue InGaN/GaN Light Emitting Diode on Nonpolarm-plane Bulk GaN Substrate. *Japanese Journal of Applied Physics*, **2007**, 46, L960-L962	1.4	81
27	Continuous-wave Operation of AlGaN-cladding-free Nonpolarm-Plane InGaN/GaN Laser Diodes. *Japanese Journal of Applied Physics*, **2007**, 46, L761-L763	1.4	71
26	Optical polarization characteristics ofm-oriented InGaN/GaN light-emitting diodes with various indium compositions in single-quantum-well structure. *Journal Physics D: Applied Physics*, **2008**, 41, 225104	3	52
25	Evaluation of Electrostatic Potential Induced by Anion-Dominated Partition into Zwitterionic Micelles and Origin of Selectivity in Anion Uptake. *Langmuir*, **2000**, 16, 9199-9204	4	52
24	Compositional Dependence of Nonpolarm-Plane InxGa1-xN/GaN Light Emitting Diodes. *Applied Physics Express*, **2008**, 1, 041101	2.4	46
23	Impact of Substrate Miscut on the Characteristic ofm-plane InGaN/GaN Light Emitting Diodes. *Japanese Journal of Applied Physics*, **2007**, 46, L1117-L1119	1.4	44
22	Comparison of InGaN/GaN light emitting diodes grown on m -plane and a -plane bulk GaN substrates. *Physica Status Solidi - Rapid Research Letters*, **2008**, 2, 89-91	2.5	42
21	Optical polarization characteristics of InGaN□GaN light-emitting diodes fabricated on GaN substrates oriented between (101□0) and (101□1□) planes. *Applied Physics Letters*, **2008**, 92, 091105	3.4	33
20	Effects of piezoelectric fields on optoelectronic properties of InGaN/GaN quantum-well light-emitting diodes prepared on nonpolar (1 0 bar1 0) and semipolar (1 1 bar{2} 2) orientations. *Journal Physics D: Applied Physics*, **2009**, 42, 135106	3	32
19	Optical polarization of m -plane In-GaN/GaN light-emitting diodes characterized via confocal microscope. *Physica Status Solidi (A) Applications and Materials Science*, **2008**, 205, 1203-1206	1.6	24
18	Effects of off-axis GaN substrates on optical properties of m-plane InGaN/GaN light-emitting diodes. *Journal of Crystal Growth*, **2008**, 310, 4968-4971	1.6	23
17	Tri-halide vapor-phase epitaxy of GaN using GaCl3on polar, semipolar, and nonpolar substrates. *Applied Physics Express*, **2016**, 9, 105501	2.4	10
16	Recent progress in nonpolar LEDs as polarized light emitters. *Physica Status Solidi (A) Applications and Materials Science*, **2009**, 206, 203-205	1.6	8
15	Simultaneous control of electrostatic micellar partition and electroosmotic flow-rate by anion-dominated partition into zwitterionic micelles. *Journal of Chromatography A*, **2001**, 920, 317-23	4.5	8
14	Thick nonpolar m-plane and semipolar (101 1) GaN on an ammonothermal seed by tri-halide vapor-phase epitaxy using GaCl3. *Journal of Crystal Growth*, **2017**, 461, 25-29	1.6	5
13	Quasiequilibrium crystal shape and kinetic Wulff plot for GaN grown by trihalide vapor phase epitaxy using GaCl3. *Physica Status Solidi (B): Basic Research*, **2017**, 254, 1600679	1.3	5
12	Evaluation of GaN substrates grown in supercritical basic ammonia. *Applied Physics Letters*, **2009**, 94, 052109	3.4	5

List of Publications

11	Recent progress of large size and low dislocation bulk GaN growth **2020**,		5
10	Thermal annealing effects on SCAATTM substrate grown toward the c- and m-directions. *Applied Physics Express*, **2019**, 12, 125502	2.4	5
9	High quality GaN crystal grown by hydride vapor-phase epitaxy on SCAATTM. *Applied Physics Express*, **2020**, 13, 085508	2.4	3
8	Thermodynamic analysis of vapor-phase epitaxy of CdTe using a metallic Cd source. *Journal of Crystal Growth*, **2017**, 470, 122-127	1.6	2
7	Annihilation mechanism of V-shaped pits in c-GaN grown by hydride vapor-phase epitaxy. *Japanese Journal of Applied Physics*, **2019**, 58, SC1011	1.4	2
6	Direct Growth of CdTe on a (211) Si Substrate with Vapor Phase Epitaxy Using a Metallic Cd Source. *Journal of Electronic Materials*, **2017**, 46, 5884-5888	1.9	2
5	Customized Filter Cube in Fluorescence Microscope Measurements of InGaN/GaN Quantum-Well Characterization. *Japanese Journal of Applied Physics*, **2009**, 48, 098003	1.4	1
4	Growth of GaN on a three-dimensional SCAATTM bulk seed by tri-halide vapor phase epitaxy using GaCl3. *Japanese Journal of Applied Physics*, **2019**, 58, SC1024	1.4	0
3	Vapor Phase Epitaxy of (133) and (211) CdTe on (211) Si Substrates Using Metallic Cd Source. *Journal of Electronic Materials*, **2019**, 48, 454-459	1.9	0
2	Growth of InGaN/GaN light emitting diodes by MOCVD with a thin tapered reactor cell. *Physica Status Solidi (A) Applications and Materials Science*, **2010**, 207, 1386-1388	1.6	
1	Dependence of surface morphology at initial growth of CdTe on the II/VI on (2 1 1) Si substrates by vapor phase epitaxy using metallic Cd source. *Journal of Crystal Growth*, **2019**, 506, 185-189	1.6	